



## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
-20V	1.9Ω @ V <sub>GS</sub> = -4.5V	-0.51A
	$2.4\Omega @ V_{GS} = -2.5V$	-0.46A
	3.4Ω @ V <sub>GS</sub> = -1.8V	-0.38A
	5.0Ω @ V <sub>GS</sub> = -1.5V	-0.31A

## Description

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$  yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

# Applications

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

#### 20V P-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features and Benefits**

- Low Package Profile
- 0.6mm × 0.4mm Package Footprint
- Low On-Resistance
- Very Low Gate Threshold Voltage: -1.0V Max
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

### **Mechanical Data**

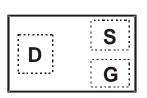
- Case: X2-DFN0604-3
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.001 grams (Approximate)



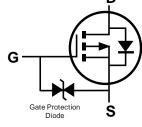
Notes:



X2-DFN0604-3



Top View Package Pin Configuration



Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMP22D5UFO-7B	X2-DFN0604-3	10,000/Tape & Reel

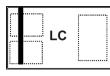
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

 See https://www.diodes.com/quality/lead-tree/ for more information about Diodes incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 Lead-free.
 Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



LC = Product Type Marking Code

Top View Bar Denotes Gate and Source Side



## Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	-20	V		
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 5) $V_{GS}$ = -4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$	ID	-0.51 -0.41	А
Pulsed Drain Current (Note 6)	I <sub>DM</sub>	-0.6	A		

## Thermal Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	Steady State	PD	0.77	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>0JA</sub>	163	°C/W
Total Power Dissipation (Note 6)	Steady State	PD	0.34	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>0JA</sub>	368	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

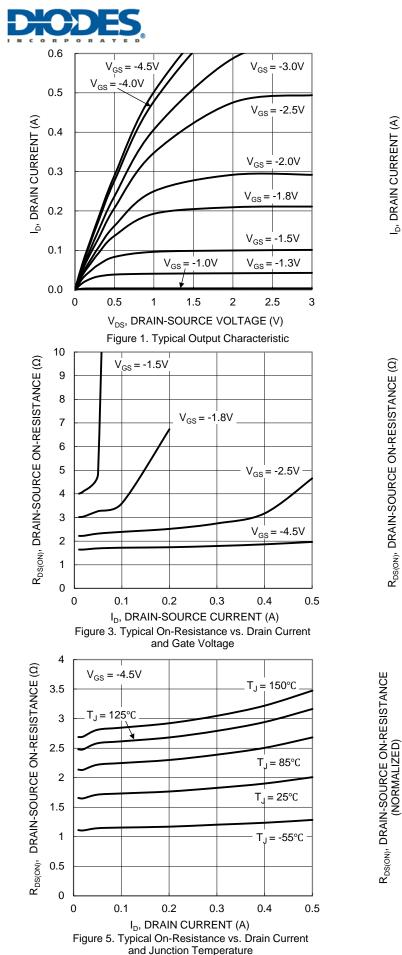
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

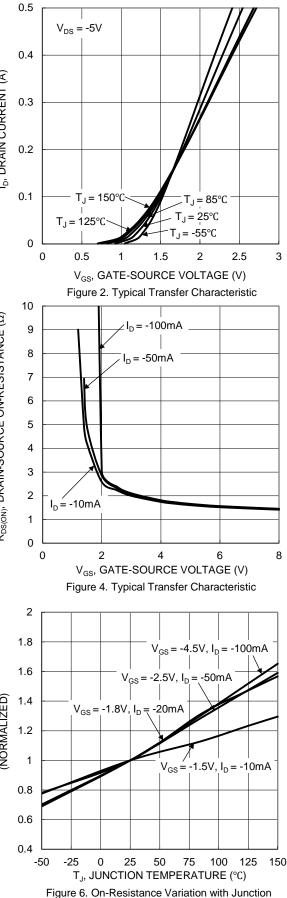
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)			71				
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_		V	$V_{GS} = 0V, I_D = -250 \mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μA	$V_{DS} = -16V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μA	$V_{GS} = \pm 5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)						·	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.4	_	-1.0	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
		_	0.95	1.9		$V_{GS} = -4.5V, I_D = -100mA$	
Static Drain-Source On-Resistance	Proven	—	1.2	2.4	0	$V_{GS} = -2.5V, I_D = -50mA$	
	Rds(on)	_	1.4	3.4	12	$V_{GS} = -1.8V, I_D = -20mA$	
		_	1.7	5.0		$V_{GS} = -1.5V, I_D = -10mA$	
Diode Forward Voltage	V <sub>SD</sub>	_	-0.5	-1.1	V	$V_{GS} = 0V, I_{S} = -10mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	—	17	—	pF		
Output Capacitance	Coss	_	4.1	_	pF	$V_{DS} = -16V, V_{GS} = 0V,$ _ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	2.7	—	pF		
Gate Resistance	Rg	_	3.3	—	kΩ	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge	Qg	_	0.3	—	nC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V, 	
Gate-Source Charge	Q <sub>gs</sub>	_	0.04		nC		
Gate-Drain Charge	Q <sub>gd</sub>	_	0.1		nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	7.3	—	ns		
Turn-On Rise Time	t <sub>R</sub>	—	20.7		ns	$V_{DD} = -15V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	185	—	ns	$R_{G} = 2\Omega, I_{D} = -200 \text{mA}$	
Turn-Off Fall Time	t <sub>F</sub>	_	97	_	ns	1	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate. Notes:

Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. 10µs pulse duty cycle = 1%.
 Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

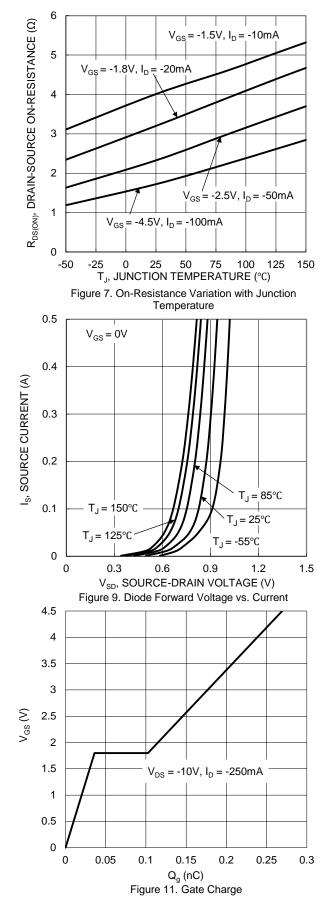


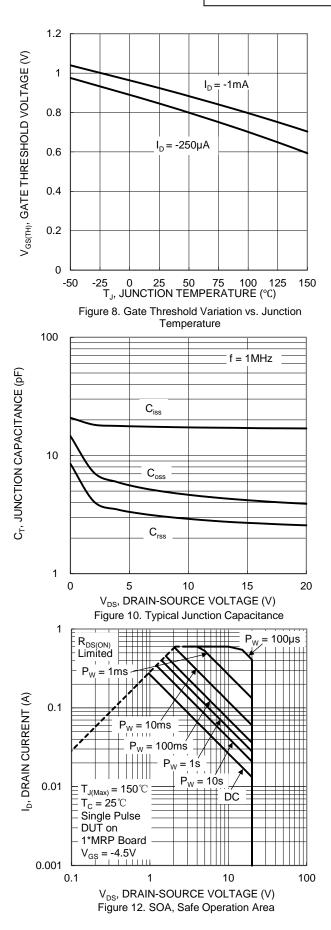


Temperature

DMP22D5UFO

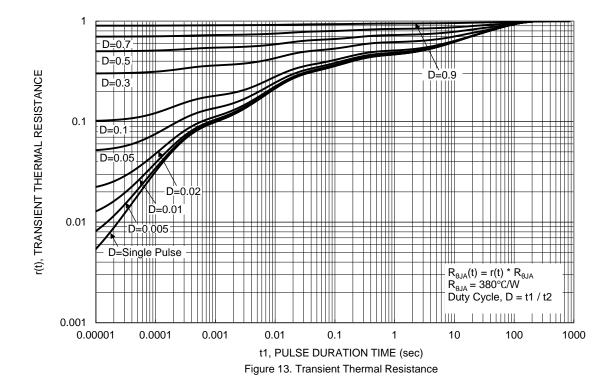






DMP22D5UFO Document number: DS41895 Rev. 4 - 2

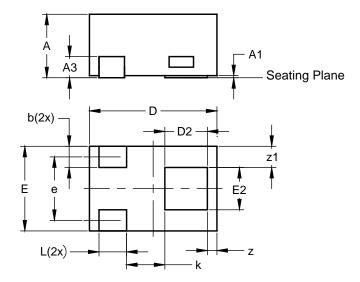






# **Package Outline Dimensions**

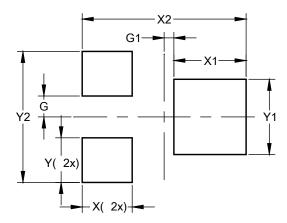
Please see http://www.diodes.com/package-outlines.html for the latest version.



X2-DFN0604-3						
Dim	Min	Max	Тур			
Α		0.40	0.36			
A1	0.00	0.03	0.02			
A3			0.10			
b	0.07	0.15	0.10			
D	0.55	0.65	0.60			
D2	0.15	0.25	0.20			
E	0.35	0.45	0.40			
E2	0.15	0.25	0.20			
е			0.30			
k	0.15					
L	0.10	0.18	0.13			
z			0.045			
z1			0.10			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)				
G	0.075				
G1	0.035				
Х	0.180				
X1	0.260				
X2	0.590				
Y	0.160				
Y1	0.270				
Y2	0.470				



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